

Tohru Nakamura

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Vertical GaN p-n Junction Diodes With High Breakdown Voltages Over 4 kV. IEEE Electron Device Letters, 2015, 36, 1180-1182.	3.9	195
2	1.7-kV and 0.55- $\text{ext}\{m\}\Omega \cdot \text{ext}\{cm\}^{\wedge}\{2\}$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. IEEE Electron Device Letters, 2016, 37, 161-164.	3.9	153
3	High-Breakdown-Voltage and Low-Specific-on-Resistance GaN p-n Junction Diodes on Free-Standing GaN Substrates Fabricated Through Low-Damage Field-Plate Process. Japanese Journal of Applied Physics, 2013, 52, 028007.	1.5	99
4	5.0 kV breakdown-voltage vertical GaN p-n junction diodes. Japanese Journal of Applied Physics, 2018, 57, 04FG09.	1.5	88
5	Formation of definite GaN p-n junction by Mg-ion implantation to n ⁻ -GaN epitaxial layers grown on a high-quality free-standing GaN substrate. Nuclear Instruments & Methods in Physics Research B, 2015, 365, 168-170.	1.4	85
6	Over 1.0-kV GaN p-n junction diodes on free-standing GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1535-1537.	1.8	79
7	Remarkable Reduction of On-Resistance by Ion Implantation in GaN/AlGaIn/GaN HEMTs With Low Gate Leakage Current. IEEE Electron Device Letters, 2007, 28, 939-941.	3.9	25
8	Fully Ion Implanted Normally-Off GaN DMOSFETs with ALD-Al ₂ O ₃ Gate Dielectrics. Materials, 2019, 12, 689.	2.9	21
9	Low interface state densities at Al ₂ O ₃ /GaN interfaces formed on vicinal polar and non-polar surfaces. Applied Physics Letters, 2020, 117, .	3.3	18
10	Characteristics of Shallow Boron-Doped Layers in Si by Rapid Vapor-Phase Direct Doping. Journal of the Electrochemical Society, 1993, 140, 1117-1121.	2.9	16
11	High-k Dielectric Passivation for GaN Diode with a Field Plate Termination. Electronics (Switzerland), 2016, 5, 15.	3.1	16
12	Ion implanted GaN MISFETs fabricated in Mg implanted layers activated by conventional rapid thermal annealing. Nuclear Instruments & Methods in Physics Research B, 2019, 449, 49-53.	1.4	12
13	Electrical properties of GaN metal-insulator-semiconductor field-effect transistors with Al ₂ O ₃ /GaN interfaces formed on vicinal Ga-polar and nonpolar surfaces. Applied Physics Letters, 2020, 117, .	3.3	12
14	Nitrogen ion implantation isolation technology for normally-off GaN MISFETs on p-GaN substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 914-917.	0.8	10
15	Ion-irradiation damage on GaN p-n junction diodes by inductively coupled plasma etching and its recovery by thermal treatment. Nuclear Instruments & Methods in Physics Research B, 2017, 409, 65-68.	1.4	7
16	Homogeneity evaluation of Mg implanted GaN layer by on-wafer forward diode current mapping. Surface and Coatings Technology, 2018, 355, 7-10.	4.8	7
17	Low-Frequency Noise Characteristics in Ion-Implanted GaN-Based HEMTs. IEEE Electron Device Letters, 2008, 29, 827-829.	3.9	6
18	Normally-off GaN MOSFETs with high-k dielectric CeO ₂ films deposited by RF sputtering. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 302-306.	0.8	5

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19	55 nm gate ion-implanted GaN-HEMTs on sapphire and Si substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2410-2412.	0.8	4
20	Effects of surface micromesas on reverse leakage current in InGaN/GaN Schottky barriers. <i>Journal of Applied Physics</i> , 2012, 112, 044505.	2.5	4
21	Impact of gate electrode formation process on Al ₂ O ₃ /GaN interface properties and channel mobility. <i>Applied Physics Express</i> , 2021, 14, 081001.	2.4	4
22	Reduction of on-resistance in ion-implanted GaN/AlGaIn/GaN HEMTs with low gate leakage current. <i>Electronics and Communications in Japan</i> , 2010, 93, 19-24.	0.5	3
23	High performance normally-off self-aligned metal gate GaN MISFETs on free-standing GaN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 918-923.	0.8	3
24	Self-aligned silicide gate GaN MISFETs with normally-off operation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2413-2415.	0.8	1
25	Large GaN p-n Junction Diodes of 3 mm in Diameter on Free-Standing GaN Substrates with High Breakdown Voltage. <i>Materials Science Forum</i> , 0, 717-720, 1299-1302.	0.3	1
26	High threshold voltage normally-off GaN MISFETs using self-alignment technique. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 858-860.	0.8	1
27	Ti/Al- GaN Reaction Mechanism Forming Low Contact Resistivity. <i>Materials Research Society Symposia Proceedings</i> , 2002, 743, L11.54.1.	0.1	0
28	Gamma-ray induced photo emission from ZnO single crystal wafer: Comparison with GaN. <i>Solid State Communications</i> , 2021, 336, 114413.	1.9	0
29	SMALL-SCALE InGaP/GaAs HETEROJUNCTION BIPOLAR TRANSISTORS FOR HIGH-SPEED AND LOW-POWER INTEGRATED-CIRCUIT APPLICATIONS. <i>Selected Topics in Electronics and Systems</i> , 2001, , 115-136.	0.2	0
30	Reduction of On-Resistance in Ion-Implanted GaN/AlGaIn/GaN HEMTs with Low Gate Leakage Current. <i>IEEJ Transactions on Electronics, Information and Systems</i> , 2008, 128, 885-889.	0.2	0
31	Improvement of Current Gain in Triple Ion Implanted 4H-SiC Bipolar Junction Transistor with Etched Extrinsic Base Regions. <i>IEEJ Transactions on Electronics, Information and Systems</i> , 2010, 130, 2188-2191.	0.2	0
32	GaN MISFETs Using Tilt Angle Ion Implantation of Magnesium. <i>IEEJ Transactions on Electronics, Information and Systems</i> , 2016, 136, 444-448.	0.2	0